

FORM PTO-1449	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No.	Application No. 10/710,608
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant Kangguo CHENG et al.	
		Filing Date 07/23/2004	Group 2812

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	US 2002/0063292 A1	5-30-2002	Armstrong et al.			
	US 2003/0032261 A1	2-13-2003	Yeh et al.			
	US 2003/0040158 A1	2-27-2003	Saitoh			
	US 2004/0238914 A1	12-2-2004	Deshpande et al.			
	US 2004/0262784 A1	12-30-2004	Doris et al.			
	US 2005/0040460 A1	2-24-2005	Chidambrao et al.			
	US 2005/0082634 A1	4-21-2005	Doris et al.			
	US 2005/0093030 A1	5-5-2005	Doris et al.			
	US 2005/0098829 A1	5-12-2005	Doris et al.			
	US 2005/0106799 A1	5-19-2005	Doris et al.			
	US 2005/0145954 A1	7-7-2005	Zhu et al.			
	US 2005/0148146 A1	7-7-2005	Doris et al.			
	US 2005/0194699 A1	9-8-2005	Belyansky et al.			
	US 2005/0236668 A1	10-27-2005	Zhu et al.			
	US 2005/0245017 A1	11-3-2005	Belyansky et al.			
	US 2005/0280051 A1	12-22-2005	Chidambrao et al.			
	US 2005/0282325 A1	12-22-2005	Belyansky et al.			
	US 2006/0027868 A1	2-9-2006	Doris et al.			
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	US 2006/0060925 A1	3-23-2006	Doris et al.			
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	6,831,292	12-14-2004	Currie et al.			
	6,717,216	4-6-2004	Doris et al.			
	6,825,529	11-30-2004	Chidambrao et al.			
	7,015,082	3-21-2006	Doris et al.			
	6,974,981	12-13-2005	Chidambrao et al.			
	6,977,194	12-20-2005	Belyansky et al.			

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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	NO
		JP 64-76755	3-22-1989	Japan		-		X

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	<i>P. H. O. 2</i>	DATE CONSIDERED	<i>11/9/08</i>
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*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
<i>MH</i>		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.					
		H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures." 1989 IEEE, Paper 6.2, pp. 140-143.					
		C.J. Huang, et al., "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors." IEEE 1991, Bipolar Circuits and Technology Meeting 7.5, pp. 170-173.					
		S.R. Sheng, et al., "Degradation and Recovery of SiGe HBTs Following Radiation and Hot-Carrier Stressing." pp. 14-15.					
		Z. Yang, et al., "Avalanche Current Induced Hot Carrier Degradation in 200 GHz SiGe Heterojunction Bipolar Transistors." pp. 1-5.					
		H. Li, et al., "Design of W-Band VCOs with High Output Power for Potential Application in 77 GHz Automotive Radar Systems." 2003, IEEE GaAs Digest, pp. 263-66.					
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		B. Doyle, et al., "Recovery of Hot-Carrier Damage in Reoxidized Nitrided Oxide MOSFETs." IEEE Electron Device Letters, vol. 13, no. 1, January 1992, pp. 38-40					
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		M. Khater, et al., "SiGe HBT Technology with Fmax/Ft = 350/300 GHz and Gate Delay Below 3.3 ps". 2004 IEEE, 4 pages.					
		J.C. Bean, et al., "GEx SI 1-x/Si Strained-Layer Superlattice Grown by Molecular Beam Epitaxy". J. Vac. Sci. Technol. A 2(2), Apr.-June 1984, pp. 436-440.					
		J.H. Van Der Merwe, "Regular Articles". Journal of Applied Physics, Volume 34, No. 1, January 1963, pp. 117-122.					
		J.W. Matthews, et al., "Defects in Epitaxial Multilayers". Journal of Crystal Growth 27 (1974), pp. 118-125.					
		Subramanian S. Iyer, et al. "Heterojunction Bipolar Transistors Using Si-Ge Alloys". IEEE Transactions on Electron Devices, Vol. 36, No. 10, October 1989, pp. 2043-2064					
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		D.C. Houghton, et al., "Equilibrium Critical Thickness for SI 1-x GEx Strained Layers on (100) Si". Appl. Phys. Lett. 56 (5), 29 January 1990, pp. 460-462					
<i>MH</i>		Q. Quyang et al., "Two-Dimensional Bandgap Engineering in a Novel Si/SiGe pMOSFET with Enhanced Device Performance and Scalability". 2000, IEEE, pp. 151-154.					
EXAMINER <i>MH</i>				DATE CONSIDERED <i>11/19/01</i>			
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JUL 27 2004
PTO-1449 (Modified)

LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		ATTY. DOCKET NO. FIS920040150US1	SERIAL NO. 10/710,608
		APPLICANT: Kangguo CHENG, et al.	
		FILING DATE: 07/23/2004	GROUP: Unassigned

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

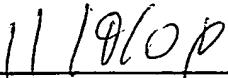
EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
MJ	6,228,694 B1	5/8/2001	Doyle et al.			
	6,406,973 B1	6/18/2002	Lee			
	6,281,532 B1	8/28/2001	Doyle et al.			
	5,683,934	11/4/97	Candelaria			
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	5,310,446	5/10/94	Konishi et al.			
	4,853,076	8/1/89	Tsaur et al.			
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	US 2002/0074598 A1	6/20/2002	Doyle et al.			
	6,509,618 B2	7/21/2003	Jan et al.			
	6,476,462 B2	11/5/2002	Shimizu et al.			
	6,362,082 B1	3/26/2002	Doyle et al.			
	6,228,694 B1	5/8/2001	Doyle et al.			
	5,565,697	10/15/96	Asakawa et al.			
	US 2003/0040158 A1	2/27/2003	Saitoh			
	US 2002/0086472 A1	7/4/2002	Roberds et al.			
	6,521,964 B1	2/18/2003	Jan et al.			
MJ	6,506,652	01/14/03	Jan et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
						YES
						NO

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		APPLICANT: Kangguo CHENG, et al.		
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REFERENCE DESIGNATION		U.S. PATENT DOCUMENTS				
EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
M.J.	5,081,513	1/14/1992	Jackson, et al.			
	3,602,841	8/31/1971	McGroddy			
	6,531,740	3/11/2003	Bosco, et al.			
	6,531,369	3/11/2003	Ozkan, et al.			
	6,501,121	12/31/2002	Yu, et al.			
	6,498,358	12/24/2002	Lach, et al.			
	6,493,497	12/10/2002	Ramdani, et al.			
	6,403,975	6/11/2002	Brunner, et al.			
	6,361,885	3/26/2002	Chou			
	6,255,169	7/3/2001	Li, et al.			
	6,246,095	6/12/2001	Brady, et al.			
	6,165,383	12/26/2000	Chou			
	6,133,071	10/17/2000	Nagai			
	6,046,464	4/4/2000	Schetzina			
M.M.	6,025,280	2/15/2000	Brady, et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
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OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

EXAMINER	<i>A. G. B.</i>	DATE CONSIDERED	<i>11/9/00</i>
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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
<i>MJ</i>	5,940,736	8/17/1999	Brady, et al.			
	5,880,040	3/9/1999	Sun, et al.			
	5,861,651	1/19/1999	Brasen, et al.			
	5,679,965	10/21/1997	Schetzina			
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	5,561,302	10/1/1996	Candelaria			
	5,471,948	12/5/1995	Burroughes, et al.			
	5,459,346	10/17/1995	Asakawa, et al.			
	5,391,510	2/21/1995	Hsu, et al.			
	5,371,399	12/6/1994	Burroughes, et al.			
	5,108,843	4/28/1992	Ohtaka, et al.			
	5,060,030	10/22/1991	Hoke			
	4,958,213	9/18/1990	Eklund, et al.			
<i>MJ</i>	4,665,415	5/12/1987	Esaki, et al.			

FOREIGN PATENT DOCUMENTS						
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
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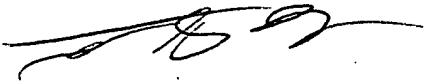
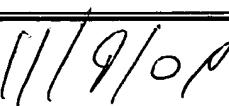
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REFERENCE DESIGNATION		U.S. PATENT DOCUMENTS				
EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
	5,989,978	11/23/1999	Peidous			
	6,284,626	9/4/2001	Kim			
	6,274,444	8/14/2001	Wang			
	6,261,964	7/17/2001	Wu, et al.			
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	5,946,559	8/31/1999	Leedy			
	5,840,593	11/24/1998	Leedy			
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FOREIGN PATENT DOCUMENTS

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REFERENCE DESIGNATION		U.S. PATENT DOCUMENTS				
EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
<i>Mly</i>	5,557,122	9/17/1996	Shrivastava, et al.			
	5,354,695	10/11/1994	Leedy			
	5,134,085	7/28/1992	Gilgen, et al.			
	5,006,913	4/9/1991	Sugahara, et al.			
	4,952,524	8/28/1990	Lee, et al.			
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	5,960,297	09-28-1999	Saki			
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	2003/0032261	02-13-2003	Yeh et al.			
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	6,265,317	07-24-2001	Chiu et al.			
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<i>NN</i>	2001/0009784	07-26-2001	Ma et al.			

FOREIGN PATENT DOCUMENTS

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						YES	NO

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EXAMINER	<i>Mly</i>	DATE CONSIDERED	<i>1/19/06</i>
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Form PTO-1449 (Modified)

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Attorney Docket No.:
FIS920040150US1Serial No.:
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Kangguo CHENG, et al.Filing Date:
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REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

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OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

<i>M. A.</i>	Kern Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si n-MOSFETs", International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.
	Kern Rim, et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs", 2002 Symposium On VLSI Technology Digest of Technical Papers, IEEE, pp 98-99.
	Gregory Scott, et al., "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress", International Electron Devices Meeting, 34.4.1, IEEE, September 1999.
	F. Ootsuka, et al., "A Highly Dense, High-Performance 130nm node CMOS Technology for Large Scale System-on-a-Chip Application", International Electron Devices Meeting, 23.5.1, IEEE, April 2000.
	Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design", International Electron Devices Meeting, 10.7.1, IEEE, April 2000.
	A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement", International Electron Devices Meeting, IEEE, March 2001.
<i>M. J.</i>	K. Ota, et al., "Novel Locally Strained Channel Technique for high Performance 55nm CMOS", International Electron Devices Meeting, 2.2.1, IEEE, February 2002.

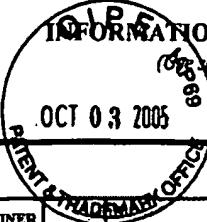
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<p style="text-align: center;">INFORMATION DISCLOSURE CITATION <small>(See several sheets if necessary)</small></p> <p style="text-align: center;">OCT 03 2005</p> 				Docket Number (Optional) FIS920040150US1		Application Number 10/710,608	
				Applicant(s) Cheng, et al.			
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MJ		3,602,841	8-31-71	McGroddy			
		4,665,415	5-12-87	Esaki, et al.			
		4,853,076	8-1-89	Tsaur, et al.			
		4,855,245	8-8-89	Neppl, et al.			
MJ		4,952,524	8-28-90	Lee, et al.			
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MJ		US 2001/0009784 A1	7-26-01	Ma, et al.			
		US 2002/0063292 A1	5-30-02	Armstrong, et al.			
		US 2002/0074598 A1	6-20-02	Doyle, et al.			
MJ		US 2002/0086472	7-4-02	Roberds, et al.			
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		JP64-76755	03-1989	Japan			YES NO
MJ							
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MJ		Kern Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si n-MOSFETs". International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.					
MJ		Kern Rim, et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs." 2002 Symposium on VLSI Technology Digest of Technical Papers, IEEE, pp. 98-99.					
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Cheng, et al.

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Group Art Unit
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U.S. PATENT DOCUMENTS

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YJ		4,958,213	9-18-90	Eklund, et al.			
YJ		5,006,913	4-9-91	Sugahara, et al.			
		5,060,030	10-22-91	Hoke, et al.			
		5,081,513	1-14-92	Jackson, et al.			
MJ		5,108,843	4-28-92	Ohtaka, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

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YJW		US 2002/0086497 A1	7-4-02	Kwok			
		US 2002/0090791 A1	7-11-02	Doyle, et al.			
		US 2003/0032261 A1	2-13-03	Yeh, et al.			
MJW		US 2003/0040158 A1	2-27-03	Saitoh			

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MJ	F. Ootsuka, et al., "A Highly Dense, High-Performance 130nm Node CMOS Technology for Large Scale System-on-a-Chip Application." International Electron Devices Meeting, 23.5.1, IEEE, April 2000.

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MM		5,391,510	2-21-95	Hsu, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

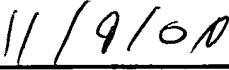
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MM		US 2003/0057184 A1	3-27-03	Yu, et al.			
NN		US 2003/0067035 A1	4-10-03	Tews, et al.			

FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

MM		Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design." International Electron Devices Meeting, 10.7.1, IEEE, April 2000.
MM		A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement." International Electron Devices Meeting, IEEE, March 2001.

EXAMINER		DATE CONSIDERED	
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INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) FIS920040150US1	Application Number 10/710,608	
				Applicant(s) Cheng, et al.		
				Filing Date 7/23/04	Group Art Unit 2812	

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
M		5,459,346	10-17-95	Asakawa, et al.			
		5,471,948	12-5-95	Burroughes, et al.			
		5,557,122	9-17-96	Shrivastava, et al.			
		5,561,302	10-1-96	Candelaria			
M		5,565,697	10-15-96	Asakawa, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

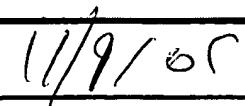
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FOREIGN PATENT DOCUMENTS

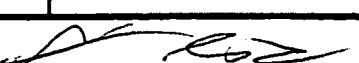
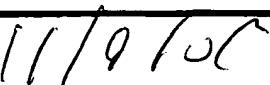
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS *(Including Author, Tide, Date, Pertinent Pages, Etc.)*

M		K. Ota, et al., "Novel Locally Strained Channel Technique for High Performance 55nm CMOS." International Electron Devices Meeting, 2.2.1, IEEE, February 2002.
M		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MJ		5,571,741	11-5-96	Leedy			
		5,592,007	1-7-97	Leedy			
		5,592,018	1-7-97	Leedy			
		5,670,798	9-23-97	Schetzina			
MJ		5,679,965	10-21-97	Schetzina			
U.S. PATENT APPLICATION PUBLICATIONS							
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OTHER DOCUMENTS <i>(Including Author, Tide, Date, Pertinent Pages, Etc.)</i>							
MJ		H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures." Paper 6.2, pp. 140-143.					
MJ		C.J. Huang, et al., "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors." IEEE 1991 Bipolar Circuits and Technology Meeting 7.5, pp. 170-173.					
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MJ		5,683,934	11-4-97	Candelaria			
		5,840,593	11-24-98	Leedy			
		5,861,651	1-19-99	Brasen, et al.			
		5,880,040	3-9-99	Sun, et al.			
		5,940,716	8-17-99	Jin, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

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FOREIGN PATENT DOCUMENTS

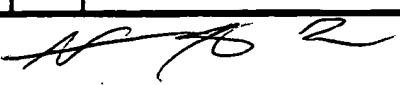
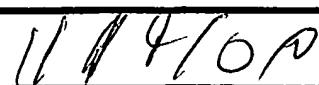
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							YES	NO

OTHER DOCUMENTS *(Including Author, Tide, Date, Pertinent Pages, Etc.)*

NM		S.R. Sheng, et al., "Degradation and Recovery of SiGe HBTs Following Radiation and Hot-Carrier Stressing." Pp. 14-15.
M2		Z. Yang, et al., "Avalanche Current Induced Hot Carrier Degradation in 200 GHz SiGe Heterojunction Bipolar Transistors." Pp. 1-5.

EXAMINER		DATE CONSIDERED	11/04/04 P
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				Applicant(s) Cheng, et al.			
				Filing Date 7/23/04	Group Art Unit 2812		
				U.S. PATENT DOCUMENTS			
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
M		5,940,736	8-17-99	Brady, et al.			
		5,946,559	8-31-99	Leedy			
		5,960,297	9-28-99	Sald			
		5,989,978	11-23-99	Peidous			
M		6,008,126	12-28-99	Leedy			
U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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						YES	NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
M		H. Li, et al., "Design of W-Band VCOs with High Output Power for Potential Application in 77 GHz Automotive Radar Systems." 2003 IEEE GaAs Digest, pp. 263-66.					
✓		H. Wurzer, et al., "Annealing of Degraded npn-Transistors- Mechanisms and Modeling." IEEE Transactions on Electron Devices, vol. 41, no. 4, April 1994, pp. S33-38.					
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				U.S. PATENT DOCUMENTS			
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>MJ</i>		6,025,280	2-15-00	Brady, et al.			
		6,046,464	4-4-00	Schetzina			
		6,066,545	5-23-00	Doshi, et al.			
		6,090,684	7-18-00	Ishitsuka, et al.			
<i>MJ</i>		6,107,143	8-22-00	Park, et al.			
U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
<i>MJ</i>		B. Doyle, et al., "Recovery of Hot-Carrier Damage in Reoxidized Nitrided Oxide MOSFETs." IEEE Electron Device Letters, vol. 13, no. 1, January 1992, pp. 38-40.					
<i>MJ</i>		H.S. Momose, et al., "Analysis of the Temperature Dependence of Hot-Carrier-Induced Degradation in Bipolar Transistors for Bi-CMOS." IEEE Transactions on Electron Devices, vol. 41, no. 6, June 1994, pp. 978-987.					
EXAMINER <i>S. B. R.</i>			DATE CONSIDERED <i>11/4/04</i>				
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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				Applicant(s) Cheng, et al.			
				Filing Date 7/23/04	Group Art Unit 2812		
				U.S. PATENT DOCUMENTS			
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MJ		6,117,722	9-12-00	Wuu, et al.			
		6,133,071	10-17-00	Nagai			
		6,165,383	12-26-00	Chou			
		6,221,735	4-24-01	Manley, et al.			
MJ		6,228,694	5-8-01	Doyle, et al.			
U.S. PATENT APPLICATION PUBLICATIONS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation
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OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
MJ		M. Khater, et al., "SiGe HBT Technology with Fmax/Ft = 350/300 GHz and Gate Delay Below 3.3 ps". 2004 IEEE, 4 pages.					
MJ		J.C. Bean, et al., "GEx SI 1-x/Si Strained-Layer Superlattice Grown by Molecular Beam Epitaxy". J. Vac. Sci. Technol. A 2(2), Apr.-June 1984, pp. 436-440.					
EXAMINER	<i>[Signature]</i>			DATE CONSIDERED		11/9/01	
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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MJ		6,246,095	6-12-01	Brady, et al.			
		6,255,169	7-3-01	Li, et al.			
		6,261,964	7-17-01	Wu, et al.			
		6,265,317	7-24-01	Chiu, et al.			
MJ		6,274,444	8-14-01	Wang			

U.S. PATENT APPLICATION PUBLICATIONS

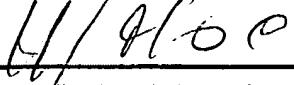
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FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

MJ		J.H. Van Der Merwe, "Regular Articles". Journal of Applied Physics, Volume 34, No. 1, January 1963, pp. 117-122.
		J.W. Matthews, et al., "Defects in Epitaxial Multilayers". Journal of Crystal Growth 27 (1974), pp. 118-125.

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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REP	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MJM		6,281,532	8-28-01	Doyle, et al.			
		6,284,623	9-4-01	Zhang, et al.			
		6,284,626	9-4-01	Kim			
		6,319,794	11-20-01	Akatsu, et al.			
MJM		6,361,885	3-26-02	Chou			

U.S. PATENT APPLICATION PUBLICATIONS

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FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

EXAMINER	Signature	Subramanian S. Iyer, et al., "Heterojunction Bipolar Transistors Using Si-Ge Alloys". IEEE Transactions on Electron Devices, Vol. 36, No. 10, October 1989, pp. 2043-2064.
		R.H.M. Van De Leur, et al., "Critical Thickness for Pseudomorphic Growth of Si/Ge Alloys and Superlattices". J. Appl. Phys. 64 (6), 15 September 1988, pp. 3043-3050.

EXAMINER	DATE CONSIDERED
<i>MJM</i>	
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INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

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Applicant(s)
 Cheng, et al.

Filing Date
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Group Art Unit
 2812

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REP	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
M		6,362,082	3-26-02	Doyle, et al.			
		6,368,931	4-9-02	Kuhn, et al.			
		6,403,486	6-11-02	Lou			
		6,403,975	6-11-02	Brunner, et al.			
M		6,406,973	6-18-02	Lee			

U.S. PATENT APPLICATION PUBLICATIONS

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						YES	NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

M		D.C. Houghton, et al., "Equilibrium Critical Thickness for Si 1-x GEx Strained Layers on (100) Si". Appl. Phys. Lett. 56 (5), 29 January 1990, pp. 460-462.

EXAMINER

DATE CONSIDERED

11/10/06

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U.S. PATENT DOCUMENTS

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WJ		6,461,936	10-8-02	von Ehrenwall			
		6,476,462	11-5-02	Shimizu, et al.			
		6,483,171	11-19-02	Forbes, et al.			
		6,493,497	12-10-02	Ramdani, et al.			
MW		6,498,358	12-24-02	Lach, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>MM</i>		6,501,121	12-31-02	Yu, et al.			
		6,506,652	1-14-03	Jan, et al.			
		6,509,618	1-21-03	Jan, et al.			
		6,521,964	2-18-03	Jan, et al.			
<i>MV</i>		6,531,369	3-11-03	Ozkan, et al.			
U.S. PATENT APPLICATION PUBLICATIONS							
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OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>M</i>		6,531,740	3-11-03	Bosco, et al.			
		6,621,392	9-16-03	Volant, et al.			
		6,635,506	10-21-03	Volant, et al.			
<i>M</i>		6,831,292	12-14-04	Currie, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

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